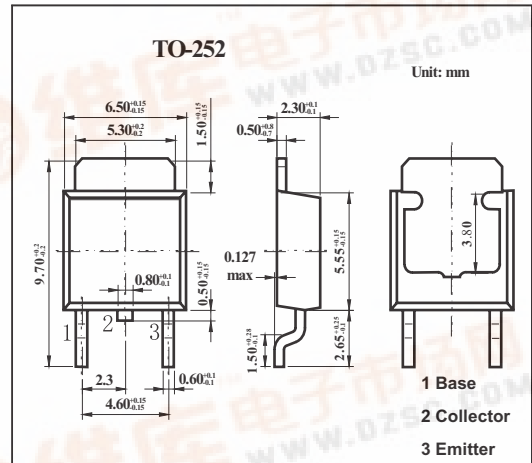


SMD Type Transistors

Silicon PNP Epitaxial Planar Type  
2SB928A

Features

- High collector to emitter  $V_{CE0}$
- High collector power dissipation  $P_c$



Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-200	V
Collector-emitter voltage	$V_{CE0}$	-180	V
Emitter-base voltage	$V_{EB0}$	-6	V
Peak collector current	$I_{CP}$	-3	A
Collector current	$I_C$	-2	A
Collector power dissipation	$P_c$	30	W
		$T_c=25^\circ C$	
		1.3	
		$T_a=25^\circ C$	
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to 150	$^\circ C$

\* Single pulse,  $P_w=10ms$

Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -200V, I_E = 0$			-50	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$			-50	$\mu A$
Collector to base voltage	$V_{CB0}$	$I_C = -500\mu A, I_E = 0$	-200			V
Collector to emitter voltage	$V_{CE0}$	$I_C = -5mA, I_B = 0$	-180			V
Emitter to base voltage	$V_{EB0}$	$I_E = -500\mu A, I_C = 0$	-6			V
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10V, I_C = -150mA$	60		240	
		$V_{CE} = -10V, I_C = -400mA$	50			
Base to emitter voltage	$V_{BE}$	$V_{CE} = -10V, I_C = -400mA$			-1	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1	V
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -0.5A, f = 10MHz$		30		MHz

hFE Classification

Rank	Q	P
$h_{FE}$	60 to 140	100 to 240

